

60V N-Channel Power MOSFET



TO-220

ITO-220

Pin Definition:

1. Gate 2. Drain

3. Source

Kev Parameter Performance

	Param	Value	Unit			
	R _{DS(on)} (max)	3	60	V		
	5 ()	V _{GS} = 10V	34			
	R _{DS(on)} (max)	$V_{GS} = 4.5V$	40	m		
•	Q _q		16.6	nC		







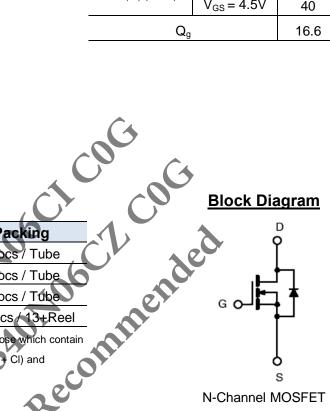


Ordering Information

Part No.	Package	Packing
TSM340N06CI C0G	ITO-220	50pcs / Tube
TSM340N06CZ C0G	TO-220	50pcs / Tube
TSM340N06CH X0G	TO-251S	75pcs / Tube
TSM340N06CP ROG	TO-252	2.5kpcs / 13+Reel

Note: %+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds



N-Channel MOSFET

Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

Parameter		Symbol		l loit		
			IPAK/DPAK	ITO-220	TO-220	Unit
Drain-Source Voltage		V _{DS}		60		V
Gate-Source Voltage		V_{GS}		±20		V
Continuous Drain Current (Note 1)	Tc = 25°C		30			Α
Continuous Drain Current	Tc = 100°C	l _D		19		Α
Pulsed Drain Current (Note 2)		I _{DM}		120		Α
Single Pulse Avalanche Energy (N	ote 3)	E _{AS}		24		mJ
Single Pulse Avalanche Current (N	Note 2)	I _{AS}		22		Α
Total Power Dissipation @ T _C = 2	5°C	P _D	40	27	66	W
Operating Junction Temperature	•	TJ		150	·	°C
Storage Temperature Range	·	T _{STG}		-55 to +150		°C



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Thermal Performance

Parameter	Symbol	Limit			Unit
rarameter	Symbol	IPAK/DPAK	ITO-220	TO-220	Uiill
Thermal Resistance - Junction to Case	R _{JC}	3.1	4.7	1.9	°C/W
Thermal Resistance - Junction to Ambient	R _{JA}		62		°C/W

Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Decision Communication Communi	$V_{GS} = 10V, I_D = 15A$	D.		28	34	
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$			33	40	m
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.2	1.7	2.5	V
Zana Cata Waltana Busin Commant	$V_{DS} = 60V, V_{GS} = 0V$	CA			1	
Zero Gate Voltage Drain Current	$V_{DS} = 48V, T_{J} = 125^{\circ}C$	I _{DSS}			10	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{OS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance	$V_{DS} = 10V, I_D = 8A$) g _{fs}	Į.	8		S
Dynamic		•	2			
Total Gate Charge (Note 4,5)		Q_g	-	16.6		
Gate-Source Charge (Note 4,5)	$V_{DS} = 30V, I_D = 20A,$ $V_{GS} = 10V$	Q_{gs}	1	2.2		nC
Gate-Drain Charge (Note 4,5)	V _{GS} = 10V	Q_{gd}		3.9		
Input Capacitance	V 20VV 0V	C _{iss}	-	1180		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	C _{oss}		68		pF
Reverse Transfer Capacitance	L= NVIP12	C_{rss}	1	45		
Gate Resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	R_g		2.1		
Switching						
Turn-On Delay Time (Note 4,5)	70	t _{d(on)}		4.6		
Turn-On Rise Time (Note 4,5)	V _{DD} =30V , V _{GS} =10V ,	t _r	1	14.8		
Turn-Off Delay Time (Note 4,5)	$R_G=6\Omega$, $I_D=-1A$	t _{d(off)}		27.2		ns
Turn-Off Fall Time (Note 4,5)		t _f	1	7.8		
Source-Drain Diode Ratings and C	haracteristic					
Continuous Drain-Source Diode	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	I _S	1		25	Α
Pulse Drain-Source Diode	V _G =V _D =0V , Force Current	I _{SM}	-		100	Α
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V _{SD}			1	V
Reverse Recovery Time (Note 4)	$V_{GS} = 0V$, $I_S = 1A$	t _{rr}		17		ns
Reverse Recovery Charge (Note 4)	$dI_F/dt = 100A/\mu s$	Q _{rr}		12		nC

Note:

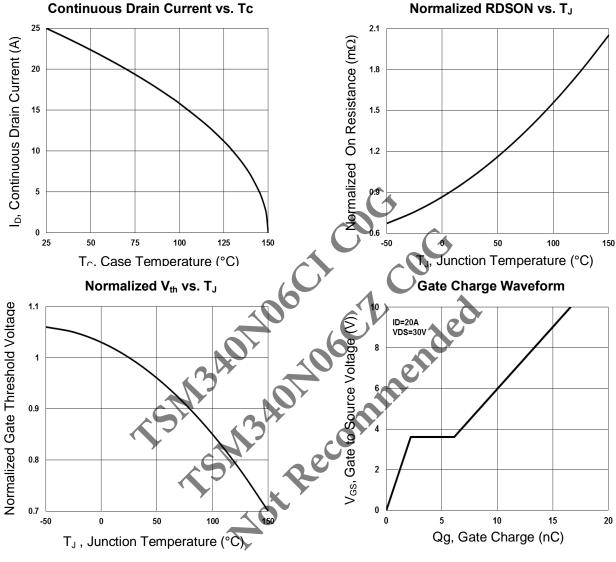
- 1. Limited by maximum junction temperature
- 2. Pulse width limited by safe operating area
- 3. L = 0.1 mH, $I_{AS} = 22 \text{A}$, $V_{DD} = 50 \text{V}$, $R_G = 25$, Starting $T_J = 25 ^{\circ}\text{C}$
- 4. Pulse test: pulse width m300µs, duty cycle m2%
- 5. Switching time is essentially independent of operating temperature.



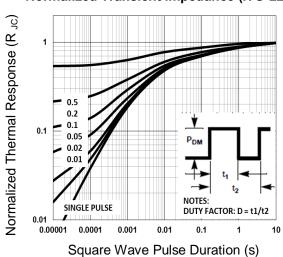
60V N-Channel Power MOSFET



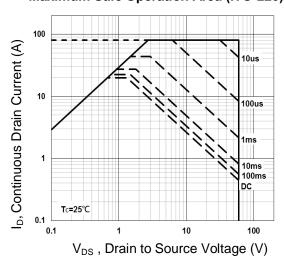
Electrical Characteristics Curve



Normalized Transient Impedance (ITO-220)



Maximum Safe Operation Area (ITO-220)



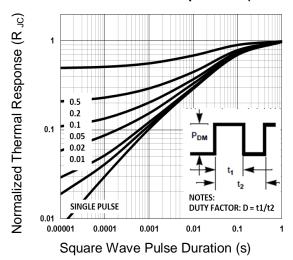


60V N-Channel Power MOSFET

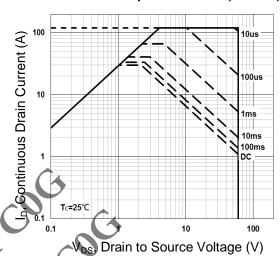


Electrical Characteristics Curve

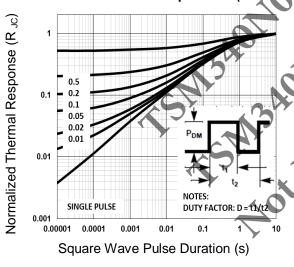
Normalized Transient Impedance (TO-220)



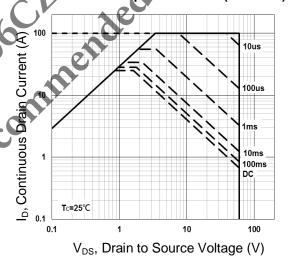
Maximum Safe Operation Area (TO-220)



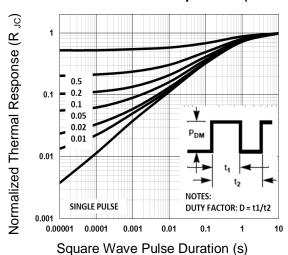
Normalized Transient Impedance (TO-2515)



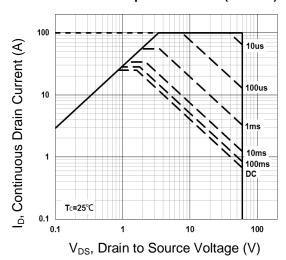
Maximum Safe Operation Area (TO-251S)



Normalized Transient Impedance (TO-252)



Maximum Safe Operation Area (TO-252)

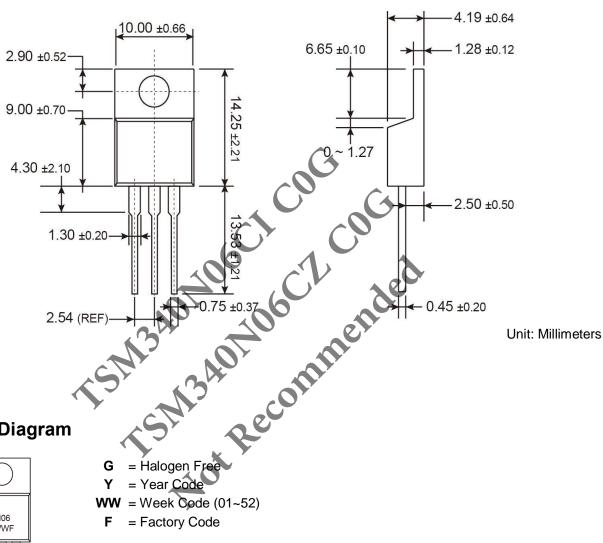








TO-220 Mechanical Drawing



Marking Diagram



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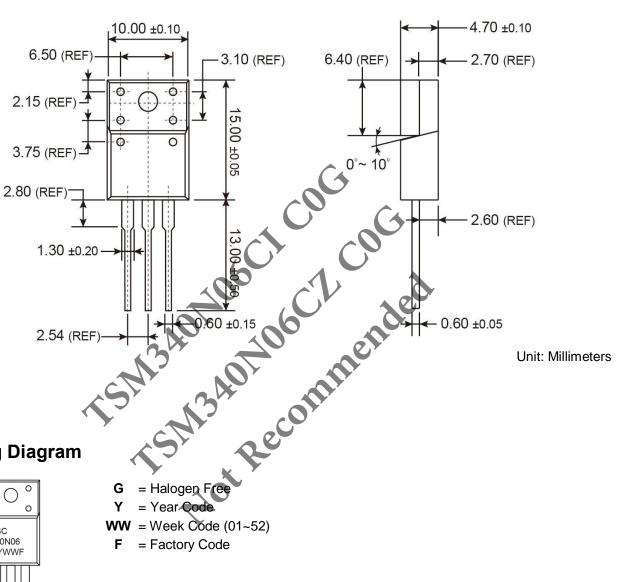
= Factory Code







ITO-220 Mechanical Drawing



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Marking Diagram



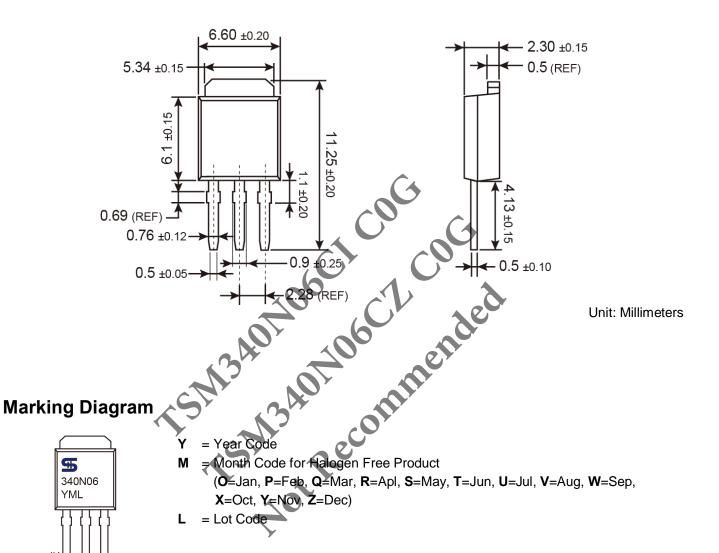
Version: D14



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TO-251S Mechanical Drawing



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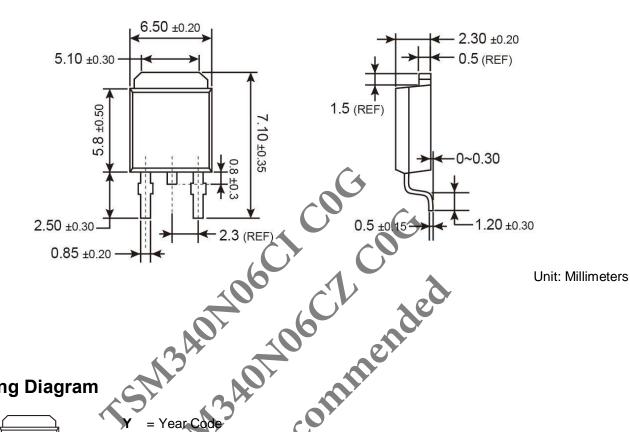
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60V N-Channel Power MOSFET



TO-252 Mechanical Drawing



Marking Diagram



= Month Code for Halogen Free Product (Q=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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= Lot Code

Version: D14



TSM340N06 60V N-Channel Power MOSFET

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